

## Product Features

- 900 ~ 930MHz (ISM band)
- 160W CW Peak Power @ 50V
- 82% Drain Efficiency @ 50V
- Excellent Ruggedness
- Excellent Thermal Stability
- Internally Matched

## Applications

- Industrial Heating and Drying
- Scientific
- Medical : Skin Treatment, Blood Therapy
- Plasma Lighting



Package Type : NS-AS01

## Description

The 150W CW RF Power Transistor is designed for Industrial, Scientific, Medical (ISM) and Plasma Lighting applications at 915MHz. This device is suitable for use in CW, pulse and linear applications. This high efficiency rugged device is targeted to replace Industrial magnetrons and other vacuum tubes currently powering industrial heating, drying, plasma lighting and medical systems.

## Typical CW Peak Power Performance ( $V_{DS}=+50V$ , $T_c=25^{\circ}C$ , $50\Omega$ )

Frequency [MHz]	Signal Type	Pin [W]	Power Gain [dB]	Drain Efficiency [%]	Pout [W]
910	CW	2.8	17.8	82.72	170
915		2.8	17.6	83.11	167.8
920		2.7	17.7	82.79	163.3

## Absolute Maximum Ratings

Rating	Symbol	Value	Unit	Condition
Drain to Source Voltage	$V_{DSS}$	150	V	$T_c=25^{\circ}C$
Gate to Source Voltage	$V_{GS}$	-10, +2	V	$T_c=25^{\circ}C$
Operating Voltage	$V_{DD}$	52	$V_{DC}$	-
Maximum Forward Gate Current	$I_{GMAX}$	24	mA	$T_c=25^{\circ}C$
Maximum Drain Current <sup>*1</sup>	$I_{DMAX}$	9	A	$T_c=25^{\circ}C$
Power Dissipation	$P_{DISS}$	90.5	W	$T_c=85^{\circ}C$
Storage Temperature	$T_{STG}$	-65, +150	$^{\circ}C$	-
Case Operating Temperature	$T_c$	-40, +150	$^{\circ}C$	-
Operating Junction Temperature <sup>*2</sup>	$T_J$	225	$^{\circ}C$	-
Soldering Temperature <sup>*3</sup>	$T_S$	245	$^{\circ}C$	-

### Note

\*1 Current Limit for long term, reliable operation.

\*2 Continuous use at maximum temperature will affect MTF.

\*3 Refer to the Application Note(AN-002) on soldering - "Solder Condition for RFHIC's GaN Device"

## Thermal Characteristics

Rating	Symbol	Value	Unit	Condition
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.54 <sup>*1</sup>	$^{\circ}C/W$	$T_c=85^{\circ}C$

### Note

\*1 Measured for the IE24150P at dissipation power is 90.5W

**Electrical Characteristics** (Tc=25°C unless otherwise noted)

Characteristics	Conditions	Symbol	Min	Typ	Max	Unit
DC Characteristics <sup>*1</sup>						
Gate Threshold Voltage	V <sub>DS</sub> = 10V	V <sub>GS(TH)</sub>	-3.8	-3.0	-2.3	V <sub>DC</sub>
	I <sub>D</sub> = 21.6mA					
Gate Quiescent Voltage	V <sub>DS</sub> = 50V	V <sub>GS(Q)</sub>	-	-3.2	-	V <sub>DC</sub>
	I <sub>D</sub> = 50mA					
Saturated Drain Current <sup>*2</sup>	V <sub>DS</sub> = 6V	I <sub>DS</sub>	18.0	21.6	-	A
	V <sub>GS</sub> = 2V					
Drain-Source Breakdown Voltage	V <sub>GS</sub> = -8V	V <sub>BR</sub>	150	-	-	V
	I <sub>D</sub> = 21.6mA					
Gate Leakage Current	V <sub>GS</sub> = -8V	I <sub>GLKG</sub>	-4.8	-	-	mA
	V <sub>DS</sub> = 120V					
Drain Leakage Current	V <sub>GS</sub> = -8V	I <sub>DLKG</sub>	-	-	8.6	mA
	V <sub>DS</sub> = 120V					
RF Characteristics (Fc = 2450MHz unless otherwise noted)						
Saturated Output Power <sup>*3</sup>	V <sub>DS</sub> = 50V	P <sub>SAT</sub>	150	160	-	W
	I <sub>DQ</sub> = 50mA					
CW Drain Efficiency <sup>*3</sup>	V <sub>DS</sub> = 50V	η	79	82	-	%
	I <sub>DQ</sub> = 50mA					
	P <sub>OUT</sub> = P <sub>SAT</sub> CW					

**Note**

\*1 Measured on wafer prior to packaging.

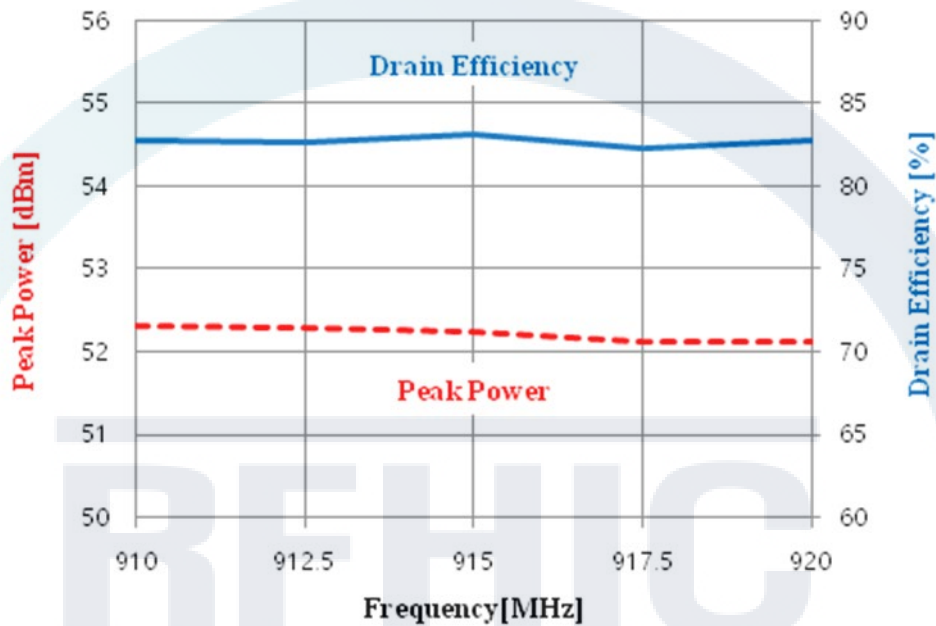
\*2 Scaled from PCM data.

\*3 CW(Continuous Wave) signal operation condition.

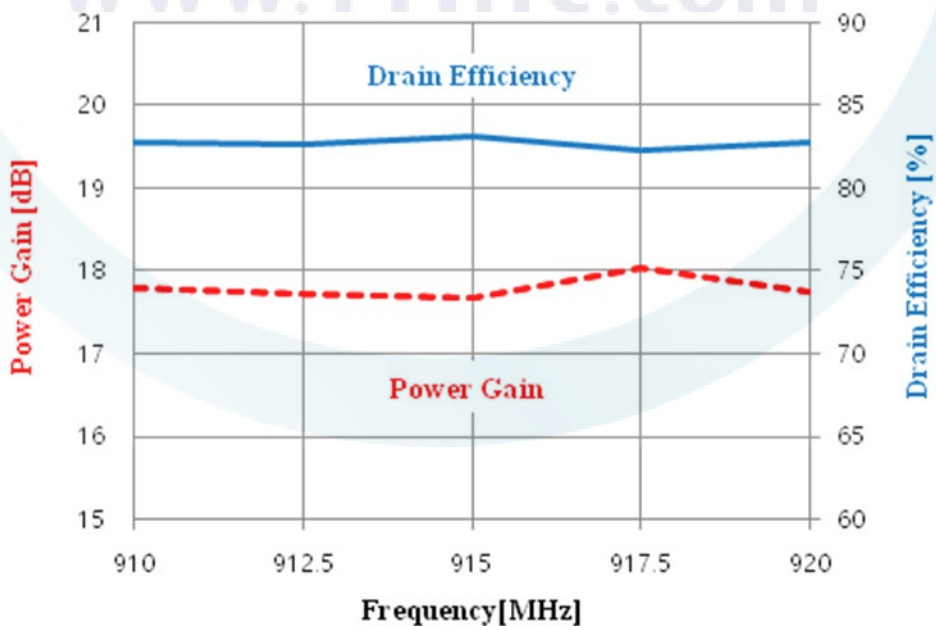
## Typical CW Performance Charts

\* Bias condition ( $I_{DQ}=50\text{mA}$  @  $V_{DS}=50\text{V}$ ,  $T_c=25^\circ\text{C}$ )

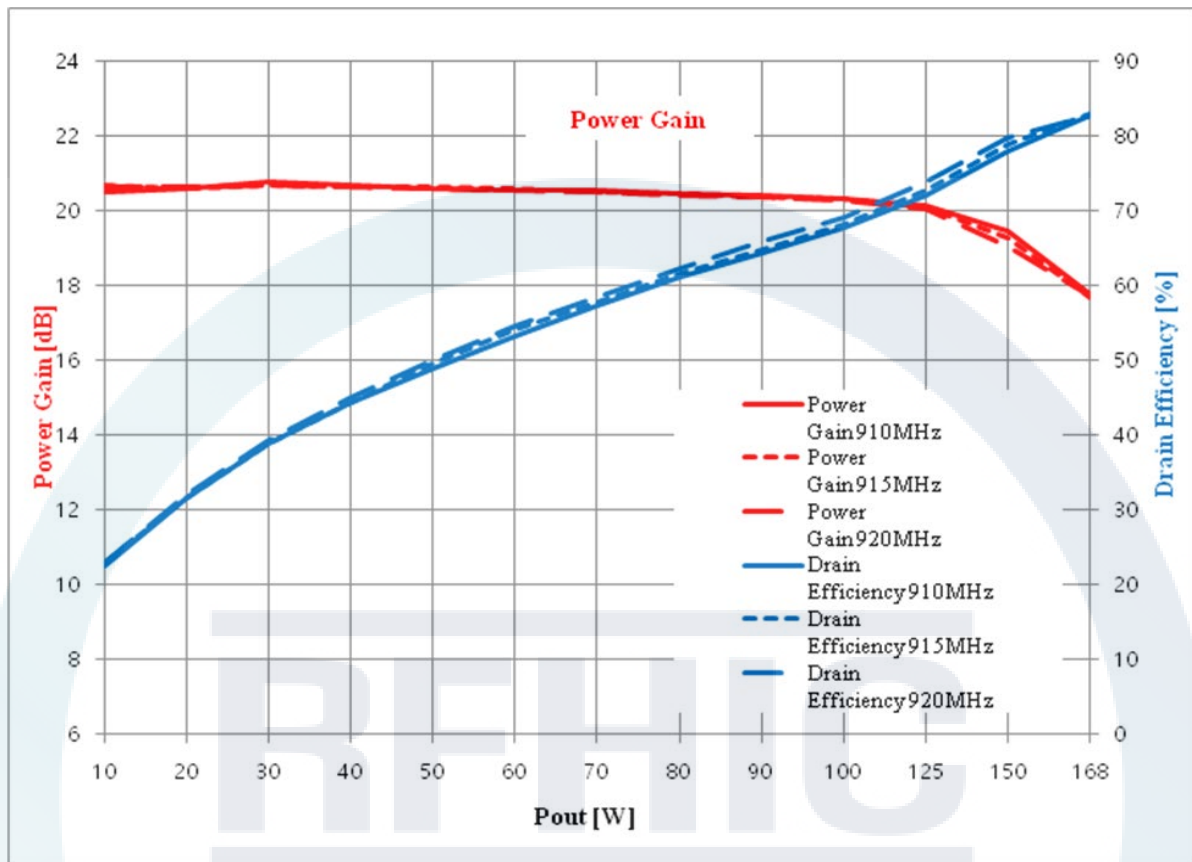
**Peak Power, Drain Efficiency vs. Frequency**



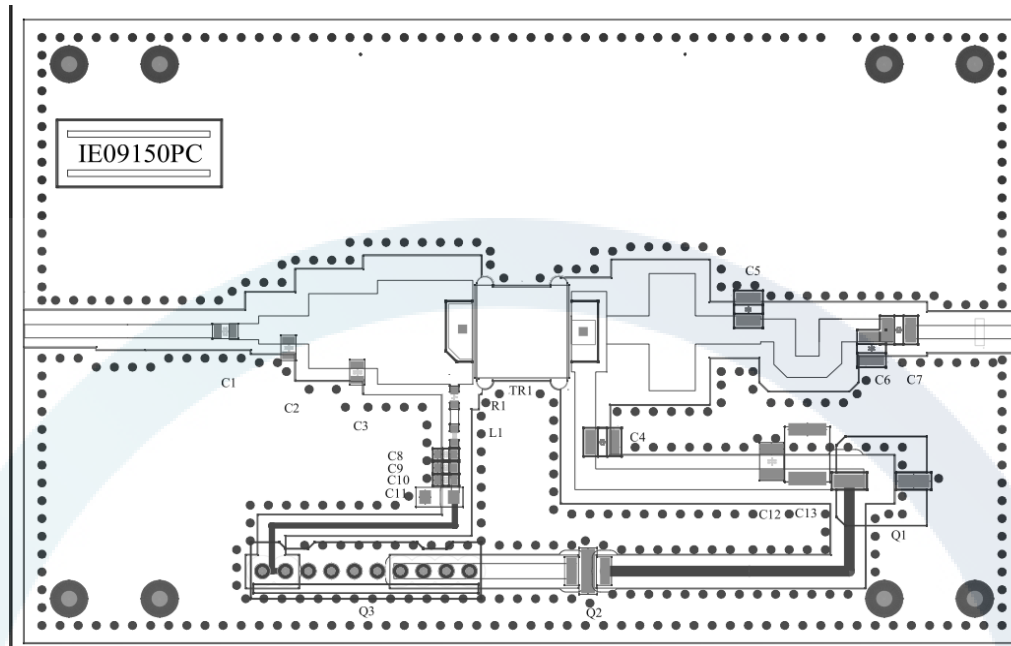
**Power Gain, Drain Efficiency vs. Frequency**



**Power Gain, Drain Efficiency vs. Output Power**



## Application Circuit

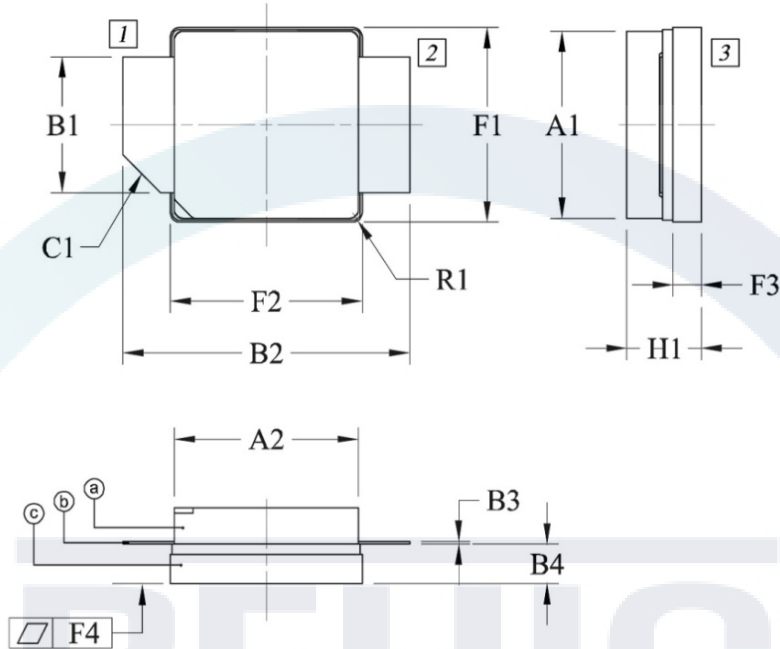


## Part List

Part	Description	Part Number	Manufacturer
L1	18nH Chip Inductor	LL1608-FSL18NJ	TOKO
R1	10 Ohm Chip Resistor, 2012	MCR10EZHJ100	ROHM
C1	100pF High Q Capacitor	201 CHA 101 JSLE	TEMEX
C2	6.8pF High Q Capacitor	201 CHA 6R8 CSLE	TEMEX
C3	2.7 pF High Q Capacitor	201 CHA 2R7 CSLE	TEMEX
C4, C12	100pF High Q Capacitor	501 CHB 101 JSLE	TEMEX
C5	2.7pF High Q Capacitor	501 CHB 2R7 CSLE	TEMEX
C6	0.9 pF High Q Capacitor	501 CHB 0R9 BSLE	TEMEX
C7	5.6 pF High Q Capacitor	501 CHB 5R6 CSLE	TEMEX
C8	100pF Chip Capacitor	GRM1885C1H101JA01D	MURATA
C9	1nF Chip Capacitor	GRM188R71H102KA01D	MURATA
C10	100nF Chip Capacitor	GRM188R71H104KA93D	MURATA
C11	10uF, 16V MLCC	C3216X7R1C106K	TDK
C13	10uF, 100V MLCC	CKG57NX7R2A106MT	TDK
Q1	33uF Aluminum Capacitor	BDS100VC33MJ10TP	SAMYOUNG
Q2	EMI FILTER	CTH32R102S20A-TM	MARUWA
Q3	DC Connector	22-04-1101	MOLEX
PCB	$\epsilon_r=3.5 \pm 0.05$ , 0.030" (0.762mm)	RF-35TC	TACONIC.
TR1	150W GaN Transistor	IE09150PC	RFHIC

**Package Dimensions (Type: NS-AS01)**

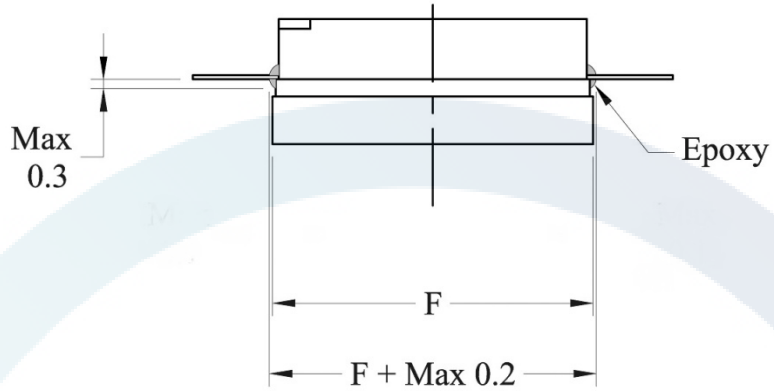
\* Unit: mm[inch] | Tolerance  $\pm 0.15$  [.006]



Pin Description		Dim.	INCH			MILLIMETER		
Pin No	Function		MIN	TYP	MAX	MIN	TYP	MAX
1	Gate	A1	.380	.384	.390	9.65	9.75	9.90
2	Drain	A2	.380	.384	.390	9.65	9.75	9.90
3	Source	B1	.274	.280	.285	6.97	7.10	7.23
		B2	.579	.598	.618	14.70	15.20	15.70
		B3	.004	.005	.007	0.10	0.13	0.18
		B4	.080	.085	.090	2.03	2.15	2.28
		C1 (Chamfer)	.075	.079	.083	1.90	2.00	2.10
		F1	.395	.400	.405	10.03	10.16	10.29
		F2	.395	.400	.405	10.03	10.16	10.29
		F3	.054	.059	.064	1.37	1.50	1.63
		F4	-	.001	-	-	0.03	-
		H1	.148	.159	.167	3.75	4.05	4.25
		L1	-	-	-	-	-	-
		L2	-	-	-	-	-	-
		R1 (Radius)	.016	.020	.024	0.40	0.50	0.60

- (a) - Lid  
 (b) - Lead Frame  
 (c) - Flange

**Sealing Epoxy Tolerance (Type : NS-DS01)**



**Note**  
Unit : mm  
F is maximum size of flange

**RFHIC**  
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**Revision History**

Part Number	Release Date	Version	Description	Data Sheet Status
IE09150PC	NOV, 2019	0.2	Modify Frequency	Preliminary
IE09150PC	AGU, 2017	0.1	Initial Release of DataSheet	Preliminary



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